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(54) **METHODS FOR FORMING
SEMICONDUCTOR REGIONS IN TRENCHES**

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See application file for complete search history.

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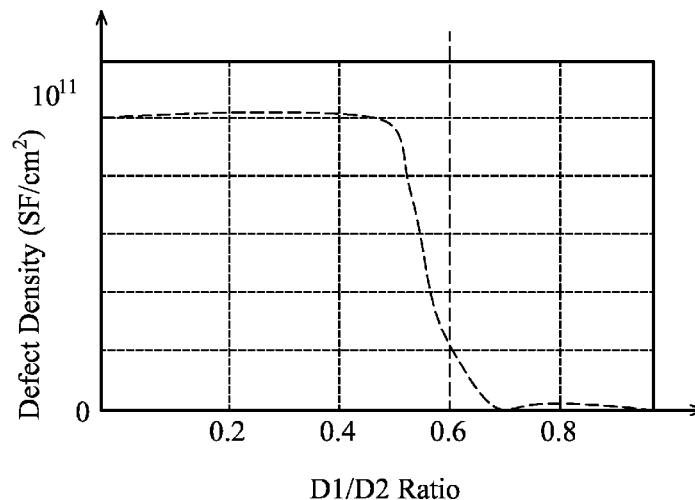
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(57) **ABSTRACT**

A structure includes a semiconductor substrate including a first semiconductor material. A portion of the semiconductor substrate extends between insulation regions in the semiconductor substrate. The portion of the semiconductor substrate has a (111) surface and a bottom surface. The (111) surface is slanted and has a top edge and a bottom edge. The bottom surface is parallel to a top surface of the insulation regions, and is connected to the bottom edge. A semiconductor region overlaps the portion of the semiconductor substrate, wherein the semiconductor region includes a second semiconductor material different from the first semiconductor material. The top edge and the bottom edge of the (111) surface are at a first depth and a second depth, respectively, relative to a top surface of the semiconductor region. A ratio of the first depth to the second depth is smaller than about 0.6.

20 Claims, 9 Drawing Sheets



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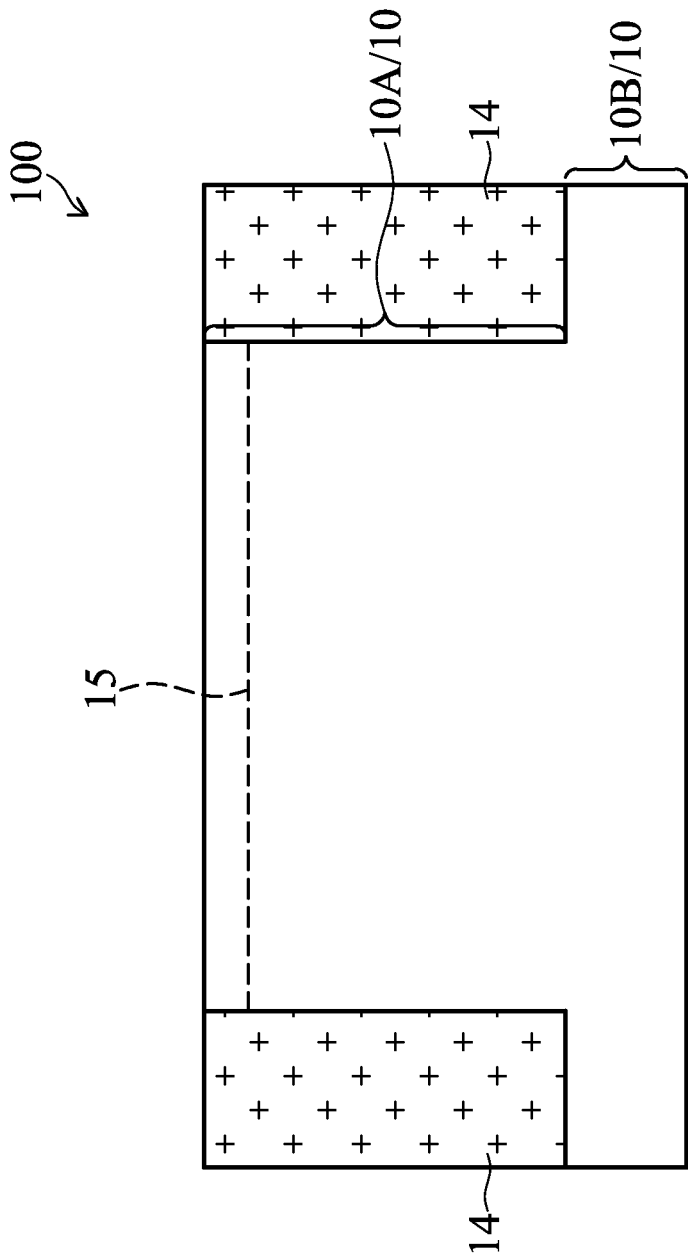


FIG. 1

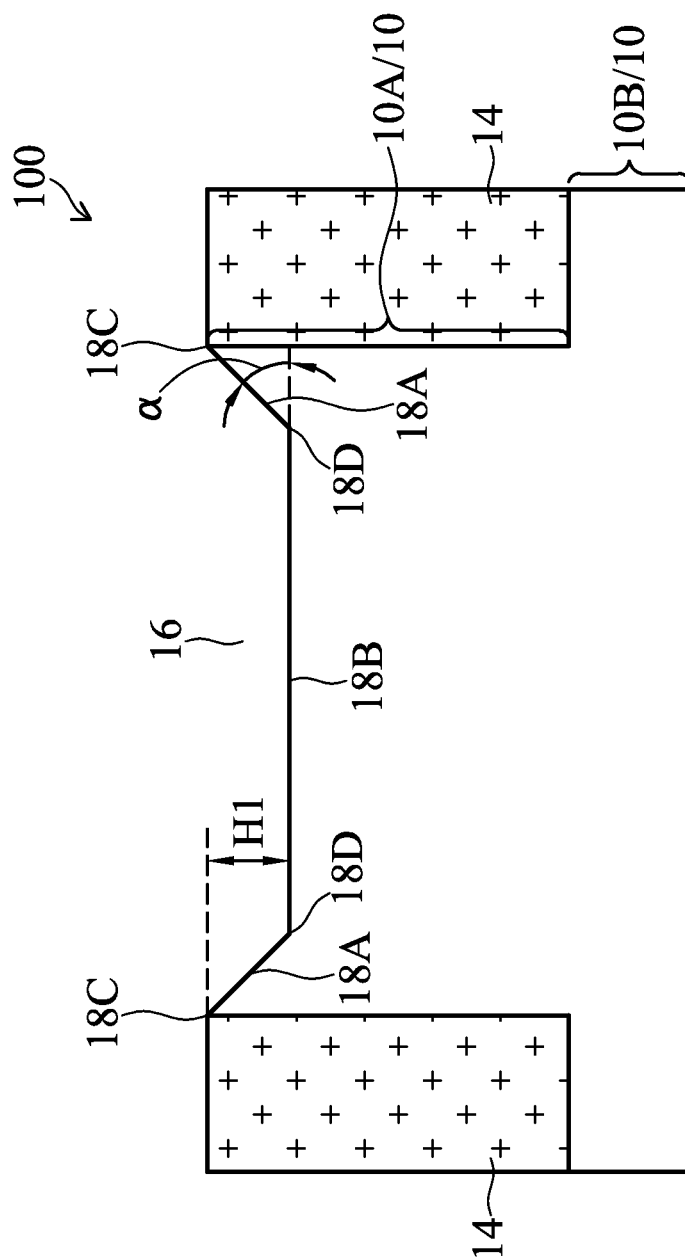


FIG. 2

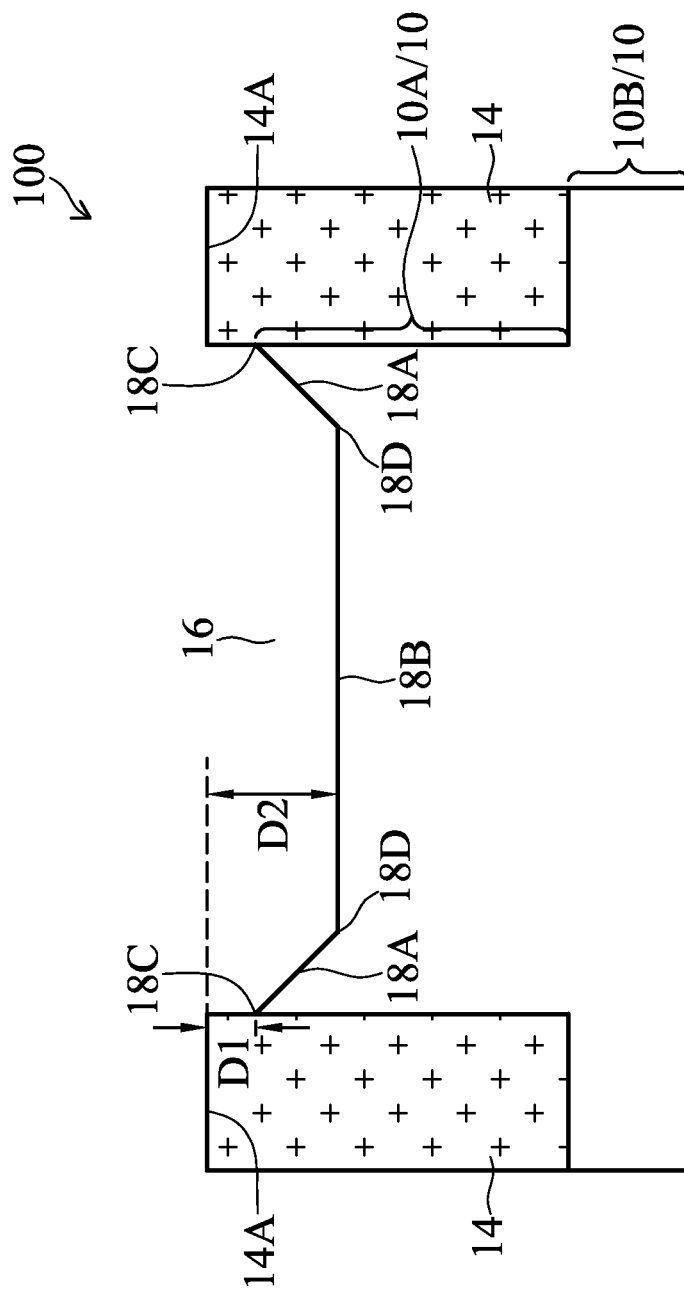


FIG. 3

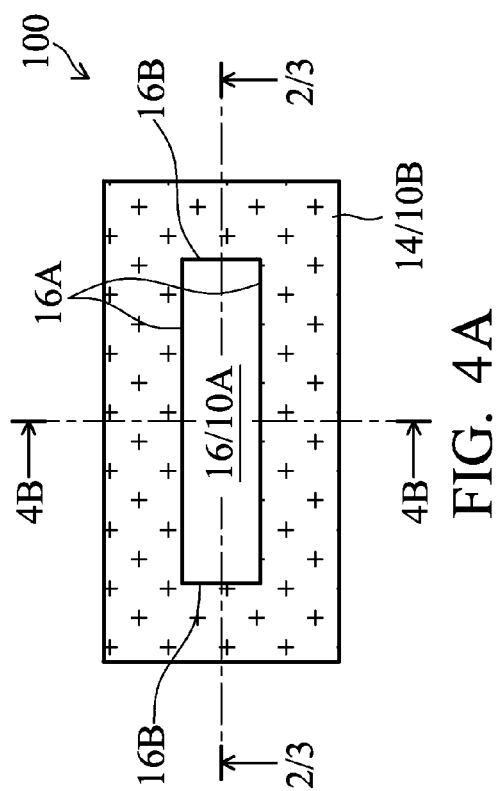


FIG. 4A

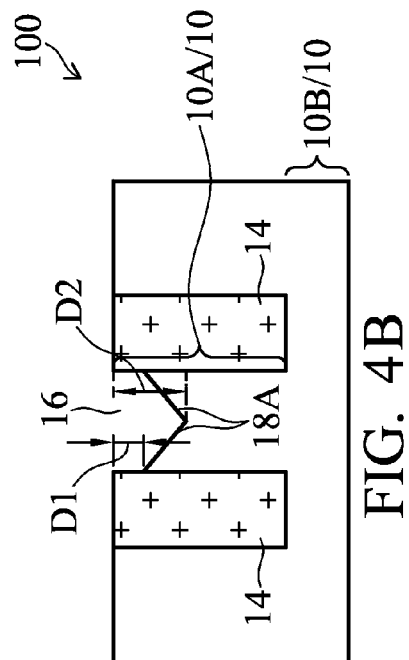


FIG. 4B

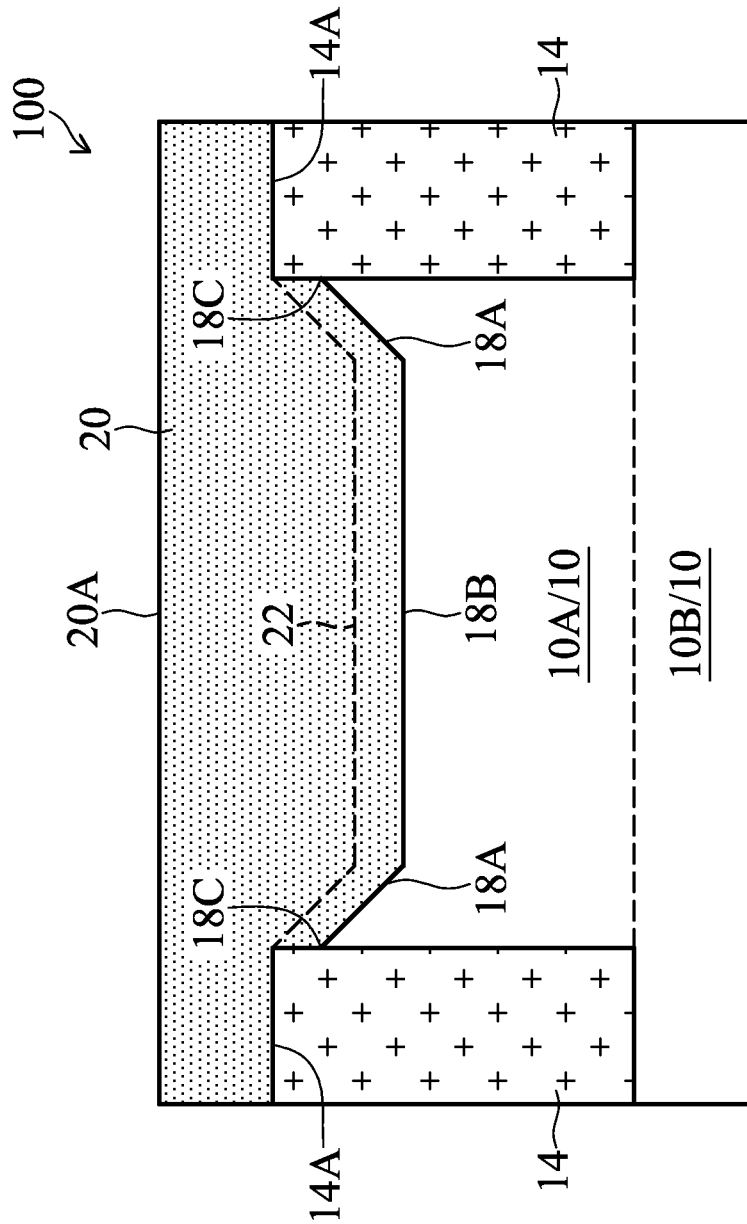


FIG. 5

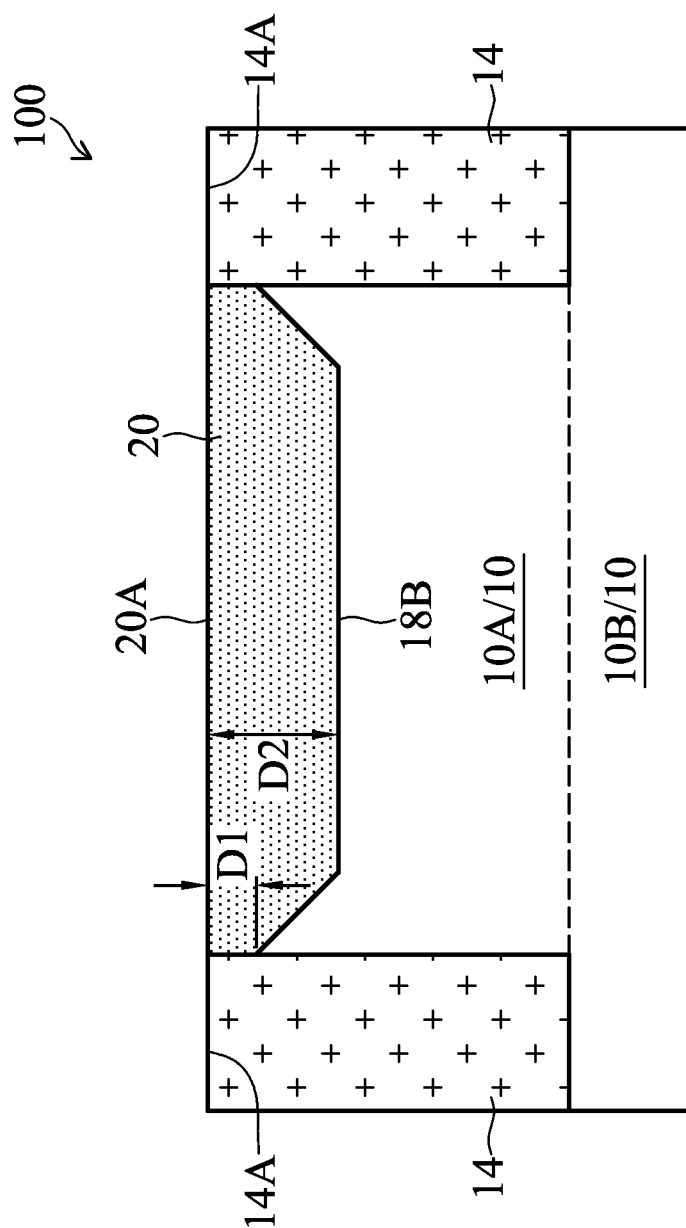


FIG. 6

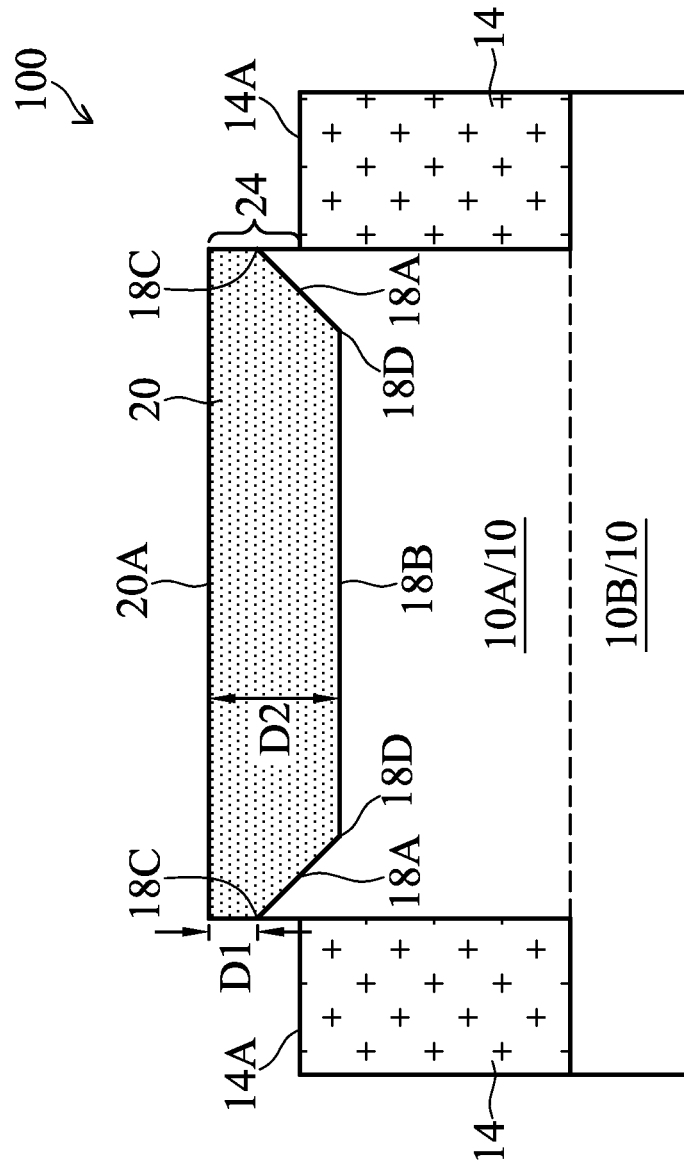


FIG. 7

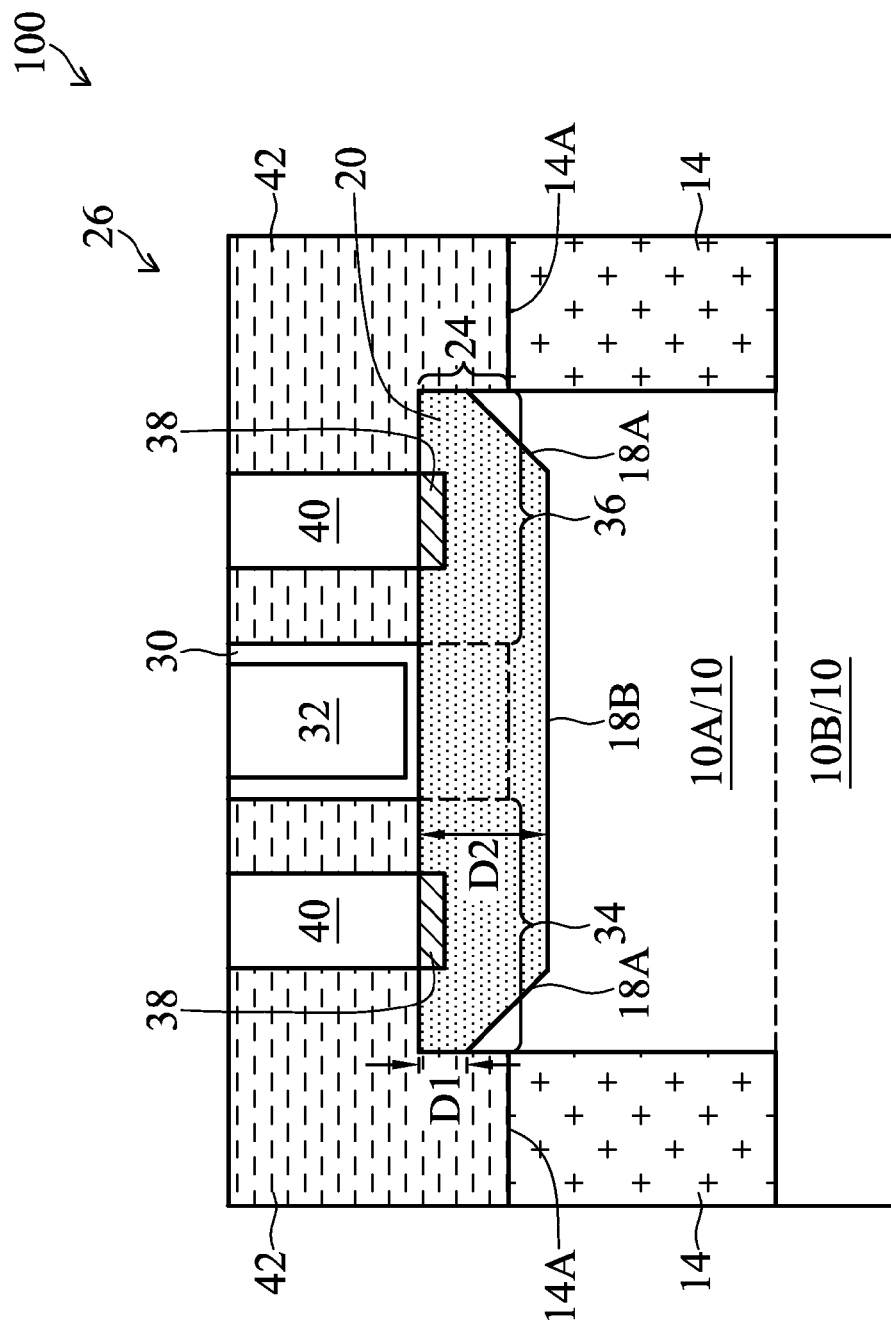


FIG. 8

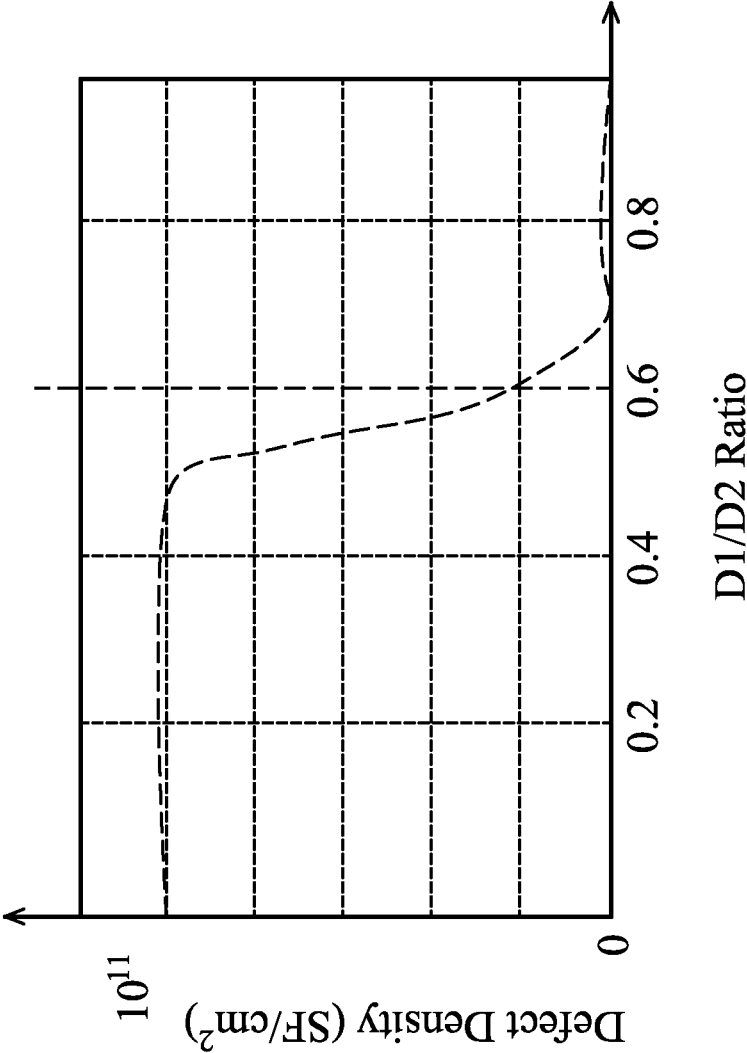


FIG. 9

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METHODS FOR FORMING SEMICONDUCTOR REGIONS IN TRENCHES

BACKGROUND

The speeds of metal-oxide-semiconductor (MOS) transistors are closely related to the drive currents of the MOS transistors, which drive currents are further closely related to the mobility of charges. For example, NMOS transistors have high drive currents when the electron mobility in their channel regions is high, while PMOS transistors have high drive currents when the hole mobility in their channel regions is high. Germanium, silicon germanium, and compound semiconductor materials of group III and group V elements (referred to as III-V compound semiconductors hereinafter) are thus good candidates for forming their high electron mobility and/or hole mobility.

A current problem posted to using germanium, silicon germanium, and III-V compound semiconductor in the integrated circuit formation processes is the difficulty in the formation of the thin films of these semiconductor materials. Currently, there is no feasible bulk growth method. Therefore, germanium, silicon germanium, and III-V compound semiconductors are commonly formed by epitaxially growing films on substrates such as Si or SiC substrates. The existing available substrate materials, however, do not have lattice constants and thermal expansion coefficients closely matching that of III-V compound semiconductors. For example, the lattice constant of silicon is about 5.43 Å, the lattice constant of germanium is about 5.66 Å, while the lattice constant of GaAs, which is a commonly used III-V compound semiconductor, is 5.65 Å. As a result, the resulting germanium-containing semiconductors and III-V compound semiconductors grown from other substrates suffer from high defect densities. Various methods were thus explored to reduce the defect densities in the grown semiconductors. A known method is to form recesses in shallow trench isolation regions, and then grow the germanium, silicon germanium, or III-V compound semiconductors in the recesses. Although the semiconductors formed using this method generally have lower defect densities than what are grown from blanket silicon wafers, the defect densities were still often high.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the embodiments, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIGS. 1 through 8 are cross-sectional views of intermediate stages in the manufacturing of a Fin Field-Effect Transistor (FinFET) in accordance with some exemplary embodiments; and

FIG. 9 illustrates the defect density in epitaxy regions as a function of a ratio of depths of recesses, in which the epitaxy regions are grown.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the embodiments of the disclosure are discussed in detail below. It should be appreciated, however, that the embodiments provide many applicable concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are illustrative, and do not limit the scope of the disclosure.

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A method of forming semiconductor materials through epitaxy re-growth in trenches is provided. The intermediate stages of forming a semiconductor fin and the respective FinFET formed on the semiconductor fin are illustrated in accordance with some embodiments. The variations of the re-growth methods in accordance with some embodiments are then discussed. Throughout the various views and illustrative embodiments, like reference numbers are used to designate like elements.

FIGS. 1 through 8 illustrate the cross-sectional views of intermediate stages in the formation of a semiconductor fin and a Fin Field-Effect Transistor (FinFET) in accordance with exemplary embodiments. Referring to FIG. 1, substrate 10, which is a part of semiconductor wafer 100, is provided. Substrate 10 may be a silicon substrate, although it may also be formed of other materials such as germanium, SiC, SiGe, GaAs, sapphire, or the like. Substrate 10 may have a (001) top surface, which is also known as (100) surface. Isolation regions such as Shallow Trench Isolation (STI) regions 14 are formed in substrate 10. Substrate 10 thus includes portions 10A between STI regions 14, and portions 10B under STI regions 14. The formation process of STI regions 14 may include etching substrate 10 to form recesses (occupied by STI regions 14), filling the recesses with a dielectric material(s), and performing a planarization (such as a Chemical Mechanical Polish (CMP)) to remove excess dielectric materials. The remaining portions of the dielectric material(s) form STI regions 14. In some embodiments, STI regions 14 comprise silicon oxide.

Portion 10A of substrate 10 is between STI regions 14, with the sidewalls of portion 10A contacting STI regions 14. In some embodiments, portion 10A comprises a silicon region free from germanium. Alternatively, portion 10A comprises silicon germanium, pure germanium, or a compound semiconductor comprising group III and group V elements (referred to as III-V compound semiconductors hereinafter). In FIG. 1, although the top surface of portion 10A is shown as being level with the top surfaces of STI regions 14, the top surface of portion 10A may also be lower than the top surfaces of STI regions 14 due to the removal of a hard mask (not shown, may be silicon nitride) and a pad oxide (not shown). Dashed line 15 is drawn to schematically illustrate the respective top surface of portion 10A.

Next, as shown in FIG. 2, a top part of portion 10A is etched to form trench 16. In some embodiments, the etching is performed through an isotropic etching such as wet etching, for example, using ammonia (NH₃), Tetra-Methyl Ammonium Hydroxide (TMAH), a potassium hydroxide (KOH) solution, or the like, as an etchant. As a result of the etching process, slant surfaces 18A are formed as parts of the top surfaces of portion 10A. In some embodiments, slant surfaces 18A are (111) surfaces on (111) surface planes. Portion 10A further includes flat surface 18B connected to the bottom edges 18D of (111) surfaces 18A, wherein edges 18D are also the end edges of flat surface 18B. In some embodiments, substrate 10 has a (001) top surface plane, and hence flat surface 18B also has a (001) surface plane. Tilt angle α of slant surfaces 18A, which tilt angle is also formed between surfaces 18A and 18B, is thus about 54.7 degrees.

In the etching steps, process conditions are adjusted, so that the (111) surfaces 18A have large areas. Height H1 of surfaces 18A may be greater than about 20 nm, wherein height H1 is measured from top edge 18C to the bottom edge 18D of surface 18A. In some embodiments, to increase the area of (111) surfaces 18A, the concentration (or percentage) of the etching solution is adjusted. For example, when TMAH is used, the concentration of TMAH in the etching solution may

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be between about 5 weight percent and about 95 weight percent. When ammonia is used, the concentration of ammonia in the etching solution may be between about 5 weight percent and about 95 weight percent. Alternatively or simultaneously, to increase the area of (111) surfaces **18A**, the temperature of the etching solution is adjusted. In some embodiments, the temperature of the etching solution is between about 28° C. and about 100° C. The various factors including the type of chemicals in the etching solution, the concentration of the chemicals in the etching solution, and the temperature in combination affect the area of (111) surfaces **18A**, and the change of one factor may need the adjustment of other factors in order to generate a large area of (111) surfaces **18A**.

In some embodiments, in the beginning stage of the etching, the middle region of portion **10A** is etched down, so that flat surface **18B** is formed. With the proceeding of the etching process, flat surface **18B** is lowered, and (111) surfaces **18A** grow in sizes. Top edges **18C** of (111) surfaces **18A**, however, may not be lowered in the beginning stage of the etching process. Top edges **18C** may be the joint points of (111) surfaces **18A** and STI regions **14**. With further etching of portion **10A**, top edges **18C** may start to be lowered, and the resulting structure is shown in FIG. 3.

FIG. 3 illustrates the continued etching of portion **10A**, so that top edges **18C** of surfaces **18A** are lowered with the proceeding of the etching process. Throughout the description, the depths of top edges **18C**, which depths are measured from top surfaces **14A** of STI regions **14** to top edges **18C**, are referred to as depth D1. The depth of flat surface **18B**, which depth is measured from top surfaces **14A** of STI regions **14**, is referred to as depth D2. In the continued etching, the areas of (111) surfaces **18A** may continue to grow, or may remain substantially unchanged.

FIGS. 4A and 4B illustrate a top view and a cross-sectional view, respectively, of the structures shown in FIGS. 2 and 3. The cross-sectional views in FIGS. 2 and 3 may be obtained from the plane crossing line 2/3-2/3 in FIG. 4A. The cross-sectional view in FIG. 4B may be obtained from the plane crossing line 4B-4B in FIG. 4A. In some embodiments, as shown in FIG. 4A, trench **16** comprises long side(s) **16A** and short side(s) **16B** shorter than long side **16A**. Short side **16B** of trench **16** may extend along, and parallel to, a <1-10> direction of substrate **10** and a <-110> direction, where in the <-110> direction is the opposite direction of the <1-10> direction. Long side **16A** of trench **16** extends along, and parallel to, the <110> direction and the <-1-10> direction of substrate **10**. In some embodiments, in the plane that is parallel to the short side **16B**, as shown in FIG. 4B, (111) surfaces **18A** merge with each other, and hence trench **16** has a V-shaped bottom. As a comparison, in the plane that is parallel to long side **16A**, as shown in FIGS. 2 and 3, two (111) surfaces **18A** appear to be separated from each other by flat surface **18B**.

Referring to FIG. 5, an epitaxy is performed, and semiconductor region **20** is re-grown in trench **16**. Top surfaces **18A** and **18B** of substrate portion **10A** thus become the interfaces between substrate portion **10A** and semiconductor region **20**. In some embodiments, semiconductor region **20** is re-grown from the structure in FIG. 2, in which the top edges **18C** of (111) surfaces **18A** are not lowered when flat surface **18B** is lowered. The respective structure is similar to what is shown in FIG. 5, except that the bottom of semiconductor region **20** is at the position illustrated by dashed line **22**. In alternative embodiments, the re-growth of semiconductor region **20** is

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performed on the structure in FIG. 3, in which top edges **18C** of (111) surfaces **18A** are lowered. The resulting structure is shown in FIG. 5.

In some embodiments, semiconductor region **20** comprises silicon germanium, with the atomic percentage of germanium greater than zero percent, and equal to or smaller than 100 percent. When the atomic percentage of germanium is 100 percent, semiconductor region **20** is formed of pure germanium. In the embodiments wherein semiconductor region **20** comprises silicon germanium, the upper portions may have greater germanium percentages than lower portions. In alternative embodiments, semiconductor region **20** comprises a III-V compound semiconductor material selected from InAs, AlAs, GaAs, InP, GaN, InGaAs, InAlAs, GaSb, AlSb, AlP, GaP, and combinations thereof. Semiconductor region **20** may be a homogenous region, with the bottom portions and the top portions formed of a same material and having the same compositions of elements. Semiconductor region **20** may also be a composite region, with bottom portions and top portions comprising different materials or having different compositions. For example, the upper portions of semiconductor region **20** may have greater lattice mismatches with substrate **10** than lower portions.

The epitaxy is continued until the top surface **20A** of semiconductor region **20** is higher than top surfaces **14A** of STI regions **14**. A planarization is then performed to remove excess portions of semiconductor region **20**, which excess portions are over top surfaces **14A** of STI regions **14**. The planarization may comprise a Chemical Mechanical Polish (CMP). In the resulting structure, top surface **20A** of semiconductor region **20** is level with top surfaces **14A** of STI regions **14**. Top surface **20A** of semiconductor region **20** may be a (001) surface. The depth D1 of top edges **18C** and depth D2 of flat surface **18B** are also marked in FIG. 6. In these embodiments, depth D1 is the depth (of top edges **18C**) measured from the top surface **20A** of semiconductor region **20**, and depth D2 is the depth (of flat surface **18B**) measured from the top surface **20A** of semiconductor region **20**.

Field-Effect Transistors (FETs) may then be formed on semiconductor region **20**. For example, FIGS. 7 and 8 illustrate the cross-sectional views in the formation of Fin Field-Effect Transistor (FET) **26** in accordance with some embodiments. Referring to FIG. 7, STI regions **14** are recessed, for example, through an etching step. A top portion of semiconductor region **20** is thus higher than top surfaces **14A** of STI regions **14**. This portion of semiconductor strip region **20** forms semiconductor fin **24**, which may be used to form FinFET **26**, as shown in FIG. 8. In some embodiments, top surfaces **14A** of STI regions **14** are higher than flat surface **18B**, and may be higher than, level with, or lower than, top edges **18C**. In alternative embodiments, top surfaces **14A** of STI regions **14** are lower than flat surface **18B**, and lower than bottom edges **18D**.

Referring to FIG. 8, gate dielectric **30** and gate electrode **32** are formed. Other components of FinFET **26** including source region **34**, drain region **36**, source and drain silicide regions **38**, source and drain contact plugs **40**, and Inter-Layer Dielectric (ILD) **42** are also formed. Gate dielectric **30** may be formed of a dielectric material such as silicon oxide, silicon nitride, an oxynitride, multi-layers thereof, and combinations thereof. Gate dielectric **30** may also comprise high-k dielectric materials. The exemplary high-k materials may have k values greater than about 4.0, or even greater than about 7.0. Gate electrode **32** may be formed of doped polysilicon, metals, metal nitrides, metal silicides, or the like. The illustrated gate dielectric **30** and gate electrode **32** have a gate-last structure, in which gate dielectric **30** and gate electrode **32** are

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formed after the formation of ILD 42. Accordingly, gate dielectric 30 comprises vertical portions between gate electrode 32 and ILD 42. In alternative embodiments, the gate dielectric and the gate electrode of FinFET 26 may also have a gate-first structure.

The resulting FinFET 26 as in FIG. 8 may also include semiconductor region 20 and the underlying substrate portion 10A. Furthermore, depths D1 and D2 are marked, wherein the details of top surfaces 18A and 18B (which are also interfaces) and depths D1 and D2 are essentially the same as in FIGS. 3 through 5, and are not repeated herein.

The performance of FinFET 26, such as the drive current Ion and the leakage currents, is related to the quality of re-grown semiconductor region 20 (FIGS. 5-8). It is preferred that the defects such as dislocations and stacking faults in semiconductor region 20 are as fewer as possible. Experiment results performed on sample silicon wafers revealed that the defect density in semiconductor region 20 is related to the area of (111) surfaces 18A, and the increase in the area of (111) surfaces 18A results in the reduction of the defect density in semiconductor region 20, and vice versa. When there is no (111) surfaces 18A formed, which means that D1 is equal to D2, the defect density is very high. The increase in the area of (111) surfaces 18A also means that the ratio D1/D2 is increased. FIG. 9 illustrates the defect (the stacking fault) density as a function of D1/D2 ratio. As shown in FIG. 9, when D1/D2 ratio is smaller than about 0.5, the defect density is high, and starts dropping significantly when D1/D2 ratio is about 0.5. When D1/D2 ratio is about 0.6 or smaller, the defect density is dropped to a very low level, and starts to stabilize. FIG. 9 also illustrates that when D1/D2 is close to about 0.7, the defect density has been stabilized at a low level. Secondary Electron Microscope (SEM) images of the regrown semiconductor regions from trenches revealed that when D1/D2 ratio is about 0.6 or smaller, the defects are confined close to interfaces 18B, and did not grow substantially with the further growth of semiconductor region 20. Accordingly, in accordance with the embodiments, as shown in FIG. 3, D1/D2 ratio is controlled to be smaller than about 0.6 in order to have a defect density. In addition, height H1 of (111) surfaces 18A may be greater than about 20 nm to maintain a low defect density.

In accordance with some embodiments, a structure includes a semiconductor substrate including a first semiconductor material. A portion of the semiconductor substrate extends between insulation regions in the semiconductor substrate. The portion of the semiconductor substrate has a (111) surface and a bottom surface. The (111) surface is slanted and has a top edge and a bottom edge. The bottom surface is parallel to a top surface of the insulation regions, and is connected to the bottom edge. A semiconductor region overlaps the portion of the semiconductor substrate, wherein the semiconductor region includes a second semiconductor material different from the first semiconductor material. The top edge and the bottom edge of the (111) surface are at a first depth and a second depth, respectively, relative to a top surface of the semiconductor region. A ratio of the first depth to the second depth is smaller than about 0.6.

In accordance with other embodiments, a structure includes a first semiconductor region and a second semiconductor region comprising different materials. The first semiconductor region has a flat surface having a first end edge and a second end edge, and a first (111) surface. The first (111) surface has a first bottom edge connected to the first end edge of the flat surface, and a first top edge higher than the first bottom edge. The first semiconductor region further includes a second (111) surface having a second bottom edge con-

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nected to the second end edge of the flat surface, and a second top edge higher than the second bottom edge. The second semiconductor region overlaps the first semiconductor region. The second semiconductor region has a bottom surface contacting the flat surface, the first (111) surface, and the second (111) surface, and a flat top surface parallel to the flat surface of the first semiconductor region. The first top edge of the first (111) surface is at a first depth of the second semiconductor region. The flat surface of the first semiconductor region is at a second depth of the second semiconductor region. The first depth and the second depth have a ratio smaller than about 0.6.

In accordance with yet other embodiments, a method includes recessing a portion of a semiconductor substrate between opposite isolation regions to form a recess. After the step of recessing, the portion of the semiconductor substrate includes a top surface. The top surface includes a flat surface, and a slant surface having a (111) surface plane. The slant surface has a bottom edge connected to the flat surface, and a top edge, wherein the top edge is at a first depth of the recess, and the bottom edge is at a second depth of the recess. The first depth and the second depth have a ratio smaller than about 0.6. The method further includes performing an epitaxy to grow a semiconductor material in the recess, wherein the semiconductor material is grown from the flat surface and the slant surface.

Although the embodiments and their advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the embodiments as defined by the appended claims. Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, and composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the disclosure. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps. In addition, each claim constitutes a separate embodiment, and the combination of various claims and embodiments are within the scope of the disclosure.

What is claimed is:

1. A structure comprising:

a semiconductor substrate comprising a first semiconductor material;

isolation regions extending into the semiconductor substrate, wherein a portion of the semiconductor substrate extends between the isolation regions, and wherein the portion of the semiconductor substrate comprises:

a (111) surface comprising a top edge and a bottom edge, wherein the (111) surface is slanted, and wherein the top edge adjoins a sidewall of the isolation regions; and

a bottom surface parallel to a top surface of the isolation regions, wherein the bottom surface is connected to the bottom edge of the (111) surface; and

a semiconductor region overlapping the portion of the semiconductor substrate, wherein the semiconductor region comprises a second semiconductor material different from the first semiconductor material, wherein the top edge of the (111) surface is at a first depth relative to

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a top surface of the semiconductor region, wherein the bottom edge of the (111) surface is at a second depth relative to the top surface of the semiconductor region, and wherein a ratio of the first depth to the second depth is smaller than about 0.6.

2. The structure of claim 1, wherein top surfaces of the isolation regions are higher than the bottom edge of the (111) surface of the semiconductor region.

3. The structure of claim 1, wherein the bottom surface of the portion of the semiconductor substrate has a (001) surface plane.

4. The structure of claim 1, wherein the semiconductor substrate is a silicon substrate, and wherein the semiconductor region comprises germanium.

5. The structure of claim 1, wherein the semiconductor substrate is a silicon substrate, and wherein the semiconductor region comprises a III-V compound semiconductor.

6. The structure of claim 1, wherein the top edge and the bottom edge of the (111) surface have a vertical distance greater than about 20 nm.

7. The structure of claim 1, wherein a top portion of the semiconductor region is higher than top surfaces of the isolation regions to form a semiconductor fin, and wherein the structure further comprises:

a gate dielectric on sidewalls and a top surface of the semiconductor fin;

a gate electrode on the gate dielectric; and

a source region and a drain region on opposite sides of the gate electrode.

8. A structure comprising:

a first semiconductor region comprising:

a flat surface having a first end edge and a second end edge;

a first (111) surface comprising a first bottom edge connected to the first end edge of the flat surface, and a first top edge higher than the first bottom edge; and

a second (111) surface comprising a second bottom edge connected to the second end edge of the flat surface, and a second top edge higher than the second bottom edge; and

a second semiconductor region comprising a semiconductor material different from a semiconductor material of the first semiconductor region, wherein the second semiconductor region overlaps the first semiconductor region, and wherein the second semiconductor region comprises:

a bottom surface contacting the flat surface, the first (111) surface, and the second (111) surface; and

a flat top surface parallel to the flat surface of the first semiconductor region, wherein the first top edge of the first (111) surface is at a first depth of the second semiconductor region, and the flat surface of the first semiconductor region is at a second depth of the second semiconductor region, and wherein the first depth and the second depth have a ratio smaller than about 0.6.

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9. The structure of claim 8 further comprising insulation regions on opposite sides of, and contacting sidewalls of, the first and the second semiconductor regions.

10. The structure of claim 9, wherein top surfaces of the insulation regions are substantially level with the flat top surface of the second semiconductor region.

11. The structure of claim 9, wherein top surfaces of the insulation regions are higher than the first bottom edge of the first (111) surface.

12. The structure of claim 8, wherein the flat surface of the first semiconductor region and the flat top surface of the second semiconductor region have (001) surface planes.

13. The structure of claim 8, wherein the first semiconductor region comprises a silicon region, and wherein the second semiconductor region comprises germanium.

14. The structure of claim 8, wherein the first semiconductor region comprises a silicon region, and wherein the second semiconductor region comprises a III-V compound semiconductor.

15. A structure comprising:

a semiconductor substrate comprising a first semiconductor material, wherein the semiconductor substrate comprises a first flat top surface, and a first and a second slant top surface joined to opposite ends of the first flat top surface; and

a semiconductor region over and contacting the first flat top surface and the first and the second slant top surfaces, wherein the semiconductor region and the semiconductor substrate are formed of different materials, and the semiconductor region comprises a second flat top surface, with the second flat top surface being higher than the first flat top surface by a first height difference, and higher than a top edge of the first slant top surface by a second height difference smaller than the first height difference.

16. The structure of claim 15, wherein a ratio of the second height difference to the first height difference is smaller than about 0.6.

17. The structure of claim 15 further comprising an isolation region contacting a portion of the semiconductor substrate having the first flat top surface and the first and the second slant top surfaces, wherein the top edge of the first slant top surface is higher than a top surface of the isolation region.

18. The structure of claim 17, wherein the semiconductor region extends to lower than the top surface of the isolation region.

19. The structure of claim 15, wherein the slant top surface is a (111) surface.

20. The structure of claim 15 further comprising:

a gate dielectric on sidewalls and the second flat top surface of the semiconductor region;

a gate electrode over the gate dielectric; and

a source region and a drain region on opposite sides of the gate electrode, wherein the source region and the drain region extend into the semiconductor region.

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